

# TPC6108

TENTATIVE

Notebook PC Applications  
 Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance:  $R_{DS(ON)} = 50 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 7.4 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = -30 \text{ V}$ )
- Enhancement-model:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V}$   
 ( $V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$ )

## Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	-30	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	-4.5	A
	Pulse (Note 1)	$I_{DP}$	-18	
Drain power dissipation(t = 5 s) (Note 2a)		$P_D$	2.2	W
Drain power dissipation(t = 5 s) (Note 2b)		$P_D$	0.7	
Single pulse avalanche energy (Note 4)		$E_{AS}$	1.3	mJ
Avalanche current		$I_{AR}$	-2.25	A
Repetitive avalanche energy Single-device value at dual operation (Note 2a, 3b, 5)		$E_{AR}$	0.22	mJ
Channel temperature		$T_{ch}$	150	°C
Storage temperature range		$T_{stg}$	-55~150	°C

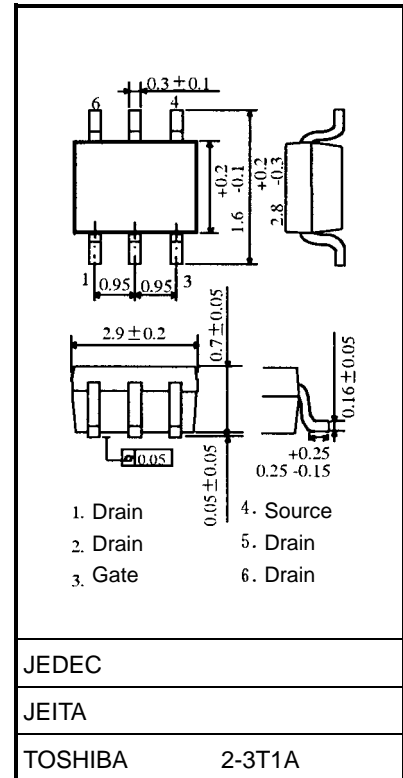
## Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient(t = 5 s) (Note 2a)	$R_{th(ch-a)}$	56.8	°C/W
Thermal resistance, channel to ambient(t = 5 s) (Note 2b)	$R_{th(ch-a)}$	178.5	°C/W

Note: For (Note 1), (Note 2), (Note 3), (Note 4) and (Note 5), please refer to the next page.

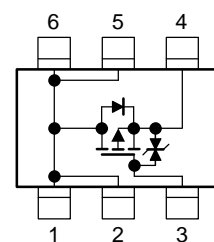
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.011 g (typ.)

## Circuit Configuration



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## Electrical Characteristics (Ta = 25°C)

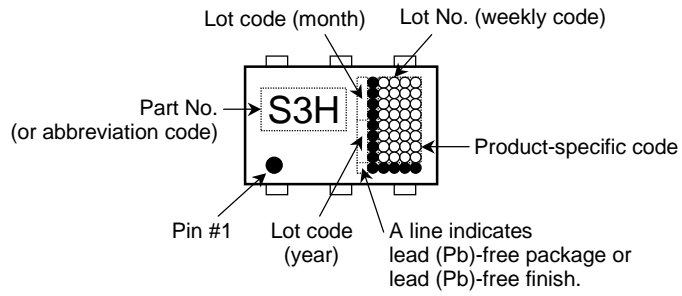
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	—	—	-10	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-30	—	—	V
		$V_{(BR)DSX}$	$I_D = -10\text{ mA}, V_{GS} = 20\text{ V}$	-15	—	—	
Gate threshold voltage		$V_{th}$	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-0.8	—	-2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}, I_D = -2.2\text{ A}$	—	75	100	m $\Omega$
		$R_{DS(ON)}$	$V_{GS} = -10\text{ V}, I_D = -2.2\text{ A}$	—	50	60	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -2.2\text{ A}$	3.7	7.4	—	S
Input capacitance		$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	570	—	pF
Reverse transfer capacitance		$C_{rss}$		—	75	—	
Output capacitance		$C_{oss}$		—	85	—	
Switching time	Rise time	$t_r$	<p><math>V_{GS} = 0\text{ V} \rightarrow -10\text{ V}</math>  <math>I_D = -2.2\text{ A}</math>  <math>R_L = 6.8\ \Omega</math>  <math>V_{DD} = -15\text{ V}</math>  <math>4.7\ \Omega</math>  <math>V_{OUT}</math>  <math>V_{DS} = -15\text{ V}</math></p>	—	3.5	—	ns
	Turn-on time	$t_{on}$		—	12	—	
	Fall time	$t_f$		—	21	—	
	Turn-off time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10\ \mu\text{s}$	—	70	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} = -24\text{ V}, V_{GS} = -10\text{ V}, I_D = -4.5\text{ A}$	—	13	—	nC
Gate-source charge1		$Q_{gs1}$		—	1.8	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	2.5	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	-18	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = -4.5\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.2	V

## Marking (Note 5)

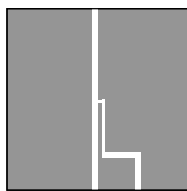
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Note 1: Ensure that the channel temperature does not exceed 150 .

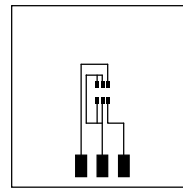
Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s)

(b) Device mounted on a glass-epoxy board (b) (t = 5 s)



(a)

FR-4  
25.4 × 25.4 × 0.8  
(Unit: mm)



(b)

FR-4  
25.4 × 25.4 × 0.8  
(Unit: mm)

Note 3:  $V_{DD} = -24\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 0.2\text{ mH}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = -2.25\text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: on lower left of the marking indicates Pin 1.

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